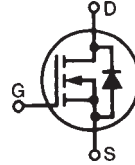


# X3-Class HiPERFET™ Power MOSFET

## IXFA38N30X3 IXFP38N30X3

$$\begin{aligned} V_{DSS} &= 300V \\ I_{D25} &= 38A \\ R_{DS(on)} &\leq 50m\Omega \end{aligned}$$

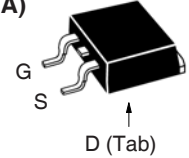
N-Channel Enhancement Mode  
Avalanche Rated



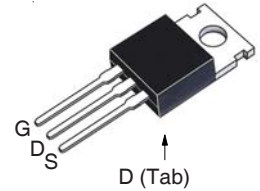
| Symbol     | Test Conditions                                                          | Maximum Ratings    |                  |
|------------|--------------------------------------------------------------------------|--------------------|------------------|
| $V_{DSS}$  | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$                          | 300                | V                |
| $V_{DGR}$  | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1M\Omega$    | 300                | V                |
| $V_{GSS}$  | Continuous                                                               | $\pm 20$           | V                |
| $V_{GSM}$  | Transient                                                                | $\pm 30$           | V                |
| $I_{D25}$  | $T_C = 25^\circ\text{C}$                                                 | 38                 | A                |
| $I_{DM}$   | $T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$               | 60                 | A                |
| $I_A$      | $T_C = 25^\circ\text{C}$                                                 | 19                 | A                |
| $E_{AS}$   | $T_C = 25^\circ\text{C}$                                                 | 400                | mJ               |
| $dv/dt$    | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ | 20                 | V/ns             |
| $P_D$      | $T_C = 25^\circ\text{C}$                                                 | 240                | W                |
| $T_J$      |                                                                          | -55 ... +150       | $^\circ\text{C}$ |
| $T_{JM}$   |                                                                          | 150                | $^\circ\text{C}$ |
| $T_{stg}$  |                                                                          | -55 ... +150       | $^\circ\text{C}$ |
| $T_L$      | Maximum Lead Temperature for Soldering                                   | 300                | $^\circ\text{C}$ |
| $T_{SOLD}$ | 1.6 mm (0.062in.) from Case for 10s                                      | 260                | $^\circ\text{C}$ |
| $F_C$      | Mounting Force (TO-263)                                                  | 10..65 / 2.2..14.6 | N/lb             |
| $M_d$      | Mounting Torque (TO-220)                                                 | 1.13 / 10          | Nm/lb.in         |
| Weight     | TO-263                                                                   | 2.5                | g                |
|            | TO-220                                                                   | 3.0                | g                |

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified) | Characteristic Values |      |                           |
|--------------|-----------------------------------------------------------------------------|-----------------------|------|---------------------------|
|              |                                                                             | Min.                  | Typ. | Max.                      |
| $BV_{DSS}$   | $V_{GS} = 0V$ , $I_D = 1mA$                                                 | 300                   |      | V                         |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 1mA$                                             | 2.5                   |      | 4.5 V                     |
| $I_{GSS}$    | $V_{GS} = \pm 20V$ , $V_{DS} = 0V$                                          |                       |      | $\pm 100$ nA              |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$ , $V_{GS} = 0V$<br>$T_J = 125^\circ\text{C}$             |                       |      | 25 $\mu A$<br>500 $\mu A$ |
| $R_{DS(on)}$ | $V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1                         |                       | 34   | 50 m $\Omega$             |

TO-263 (IXFA)



TO-220 (IXFP)



G = Gate      D = Drain  
S = Source    Tab = Drain

### Features

- International Standard Packages
- Low  $R_{DS(ON)}$  and  $Q_G$
- Avalanche Rated
- Low Package Inductance

### Advantages

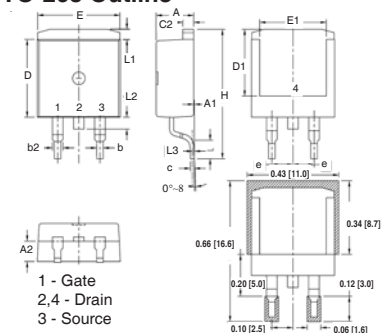
- High Power Density
- Easy to Mount
- Space Savings

### Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

| Symbol<br>(T <sub>J</sub> = 25°C, Unless Otherwise Specified) | Test Conditions                                                                                                                              | Characteristic Values                                            |      |           |
|---------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------|------|-----------|
|                                                               |                                                                                                                                              | Min.                                                             | Typ. | Max       |
| <b>g<sub>fs</sub></b>                                         | V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> , Note 1                                                                      | 20                                                               | 34   | S         |
| <b>R<sub>Gi</sub></b>                                         | Gate Input Resistance                                                                                                                        |                                                                  | 1.9  | Ω         |
| <b>C<sub>iss</sub></b>                                        | V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V, f = 1MHz                                                                                        |                                                                  | 2240 | pF        |
| <b>C<sub>oss</sub></b>                                        |                                                                                                                                              |                                                                  | 330  | pF        |
| <b>C<sub>rss</sub></b>                                        |                                                                                                                                              |                                                                  | 1.3  | pF        |
| <b>Effective Output Capacitance</b>                           |                                                                                                                                              |                                                                  |      |           |
| <b>C<sub>o(er)</sub></b>                                      | Energy related                                                                                                                               | V <sub>GS</sub> = 0V<br>V <sub>DS</sub> = 0.8 • V <sub>DSS</sub> | 130  | pF        |
| <b>C<sub>o(tr)</sub></b>                                      | Time related                                                                                                                                 |                                                                  | 520  | pF        |
| <b>Resistive Switching Times</b>                              |                                                                                                                                              |                                                                  |      |           |
| <b>t<sub>d(on)</sub></b>                                      | V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub><br>R <sub>G</sub> = 10Ω (External) |                                                                  | 19   | ns        |
| <b>t<sub>r</sub></b>                                          |                                                                                                                                              |                                                                  | 23   | ns        |
| <b>t<sub>d(off)</sub></b>                                     |                                                                                                                                              |                                                                  | 60   | ns        |
| <b>t<sub>f</sub></b>                                          |                                                                                                                                              |                                                                  | 14   | ns        |
| <b>Q<sub>g(on)</sub></b>                                      | V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub>                                    |                                                                  | 35   | nC        |
| <b>Q<sub>gs</sub></b>                                         |                                                                                                                                              |                                                                  | 10   | nC        |
| <b>Q<sub>gd</sub></b>                                         |                                                                                                                                              |                                                                  | 11   | nC        |
| <b>R<sub>thJC</sub></b>                                       | TO-220                                                                                                                                       |                                                                  |      | 0.52 °C/W |
| <b>R<sub>thCS</sub></b>                                       |                                                                                                                                              |                                                                  | 0.50 | °C/W      |

## TO-263 Outline



| SYM  | INCHES   |      | MILLIMETER |       |
|------|----------|------|------------|-------|
|      | MIN      | MAX  | MIN        | MAX   |
| A    | .170     | .185 | 4.30       | 4.70  |
| A1   | .000     | .008 | 0.00       | 0.20  |
| A2   | .091     | .098 | 2.30       | 2.50  |
| b    | .028     | .035 | 0.70       | 0.90  |
| b2   | .046     | .060 | 1.18       | 1.52  |
| C    | .018     | .024 | 0.45       | 0.60  |
| C2   | .049     | .060 | 1.25       | 1.52  |
| D    | .340     | .370 | 8.63       | 9.40  |
| D1   | .300     | .327 | 7.62       | 8.30  |
| E    | .380     | .410 | 9.65       | 10.41 |
| E1   | .270     | .330 | 6.86       | 8.38  |
| [e]  | .100 BSC |      | 2.54 BSC   |       |
| H    | .580     | .620 | 14.73      | 15.75 |
| L    | .075     | .105 | 1.91       | 2.67  |
| L1   | .039     | .060 | 1.00       | 1.52  |
| L2   | —        | .070 | —          | 1.77  |
| [L3] | .010 BSC |      | 0.254 BSC  |       |

## Source-Drain Diode

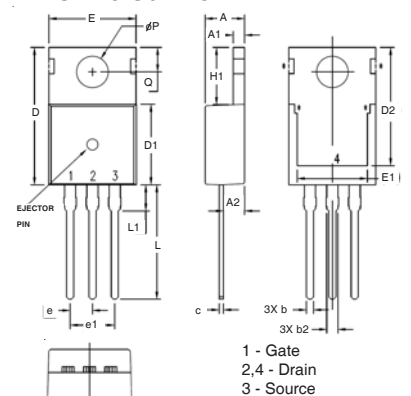
| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)    | Characteristic Values |      |       |
|----------|--------------------------------------------------------------------------------|-----------------------|------|-------|
|          |                                                                                | Min.                  | Typ. | Max   |
| $I_S$    | $V_{GS} = 0\text{V}$                                                           |                       |      | 38 A  |
| $I_{SM}$ | Repetitive, pulse Width Limited by $T_{JM}$                                    |                       |      | 152 A |
| $V_{SD}$ | $I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1                                    |                       |      | 1.4 V |
| $t_{rr}$ | $I_F = 19\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$<br>$V_R = 100\text{V}$ |                       | 90   | ns    |
| $Q_{RM}$ |                                                                                |                       | 330  | nC    |
| $I_{RM}$ |                                                                                |                       | 7.4  | A     |

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

## PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

## TO-220 Outline

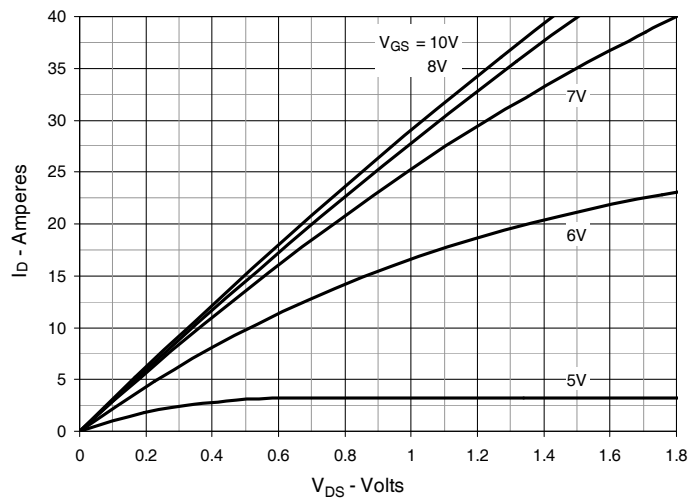


| SYM  | INCHES   |      | MILLIMETERS |       |
|------|----------|------|-------------|-------|
|      | MIN      | MAX  | MIN         | MAX   |
| A    | .169     | .185 | 4.30        | 4.70  |
| A1   | .047     | .055 | 1.20        | 1.40  |
| A2   | .079     | .106 | 2.00        | 2.70  |
| b    | .024     | .039 | 0.60        | 1.00  |
| b2   | .045     | .057 | 1.15        | 1.45  |
| c    | .014     | .026 | 0.35        | 0.65  |
| D    | .587     | .626 | 14.90       | 15.90 |
| D1   | .335     | .370 | 8.50        | 9.40  |
| (D2) | .500     | .531 | 12.70       | 13.50 |
| E    | .382     | .406 | 9.70        | 10.30 |
| (E1) | .283     | .323 | 7.20        | 8.20  |
| e    | .100 BSC |      | 2.54 BSC    |       |
| e1   | .200 BSC |      | 5.08 BSC    |       |
| H1   | .244     | .268 | 6.20        | 6.80  |
| L    | .492     | .547 | 12.50       | 13.90 |
| L1   | .110     | .154 | 2.80        | 3.90  |
| ØP   | .134     | .150 | 3.40        | 3.80  |
| Q    | .106     | .126 | 2.70        | 3.20  |

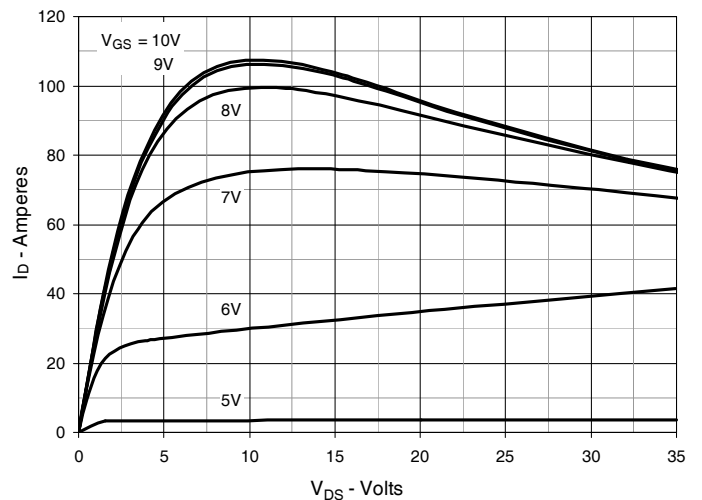
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

|                                                                                  |           |           |           |           |             |             |             |             |             |             |
|----------------------------------------------------------------------------------|-----------|-----------|-----------|-----------|-------------|-------------|-------------|-------------|-------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665   | 6,404,065B1 | 6,683,344   | 6,727,585   | 7,005,734B2 | 7,157,338B2 |
|                                                                                  | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123B1 | 6,534,343   | 6,710,405B2 | 6,759,692   | 7,063,975B2 |             |
|                                                                                  | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728B1 | 6,583,505   | 6,710,463   | 6,771,478B2 | 7,071,537   |             |

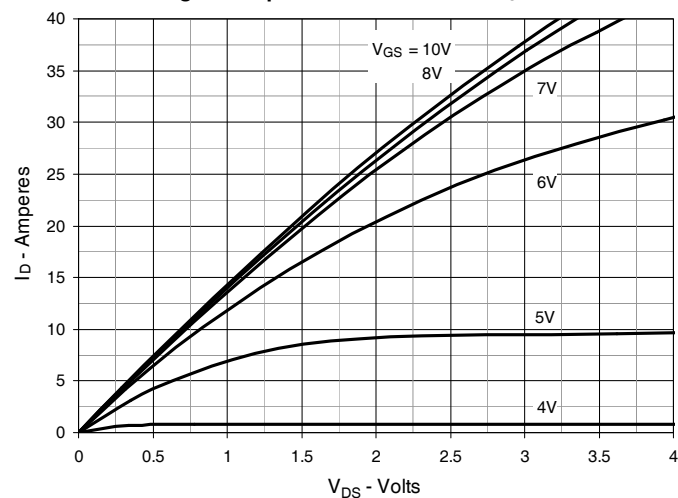
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



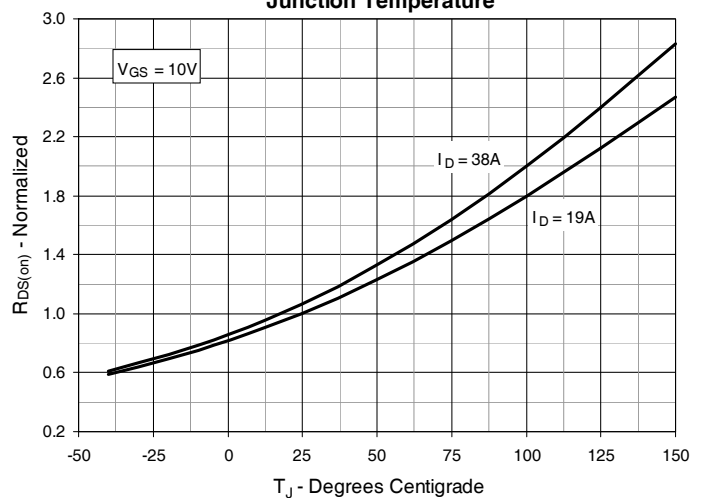
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



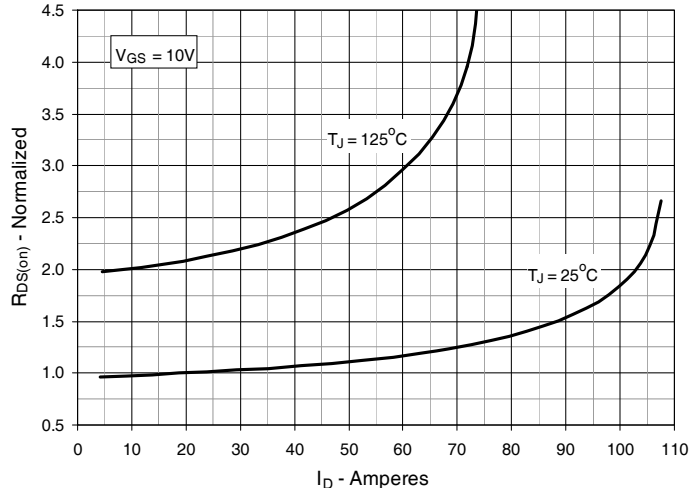
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



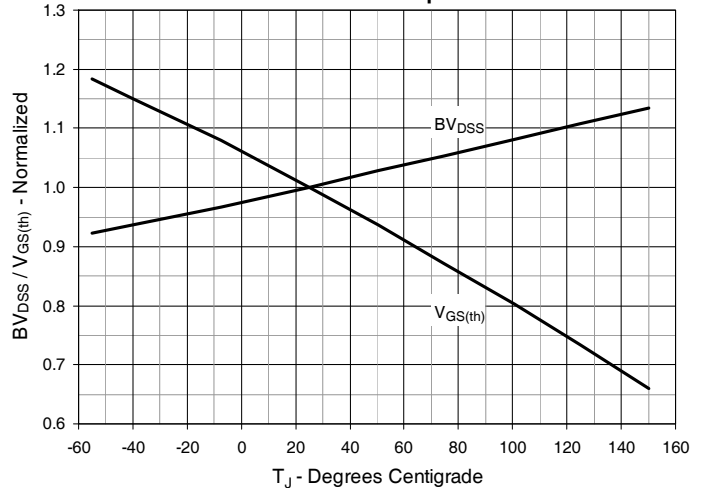
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 19\text{A}$  Value vs. Junction Temperature**



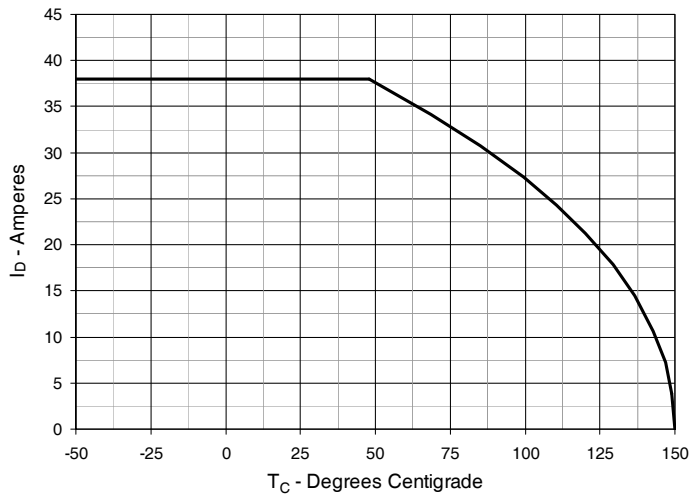
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 19\text{A}$  Value vs. Drain Current**



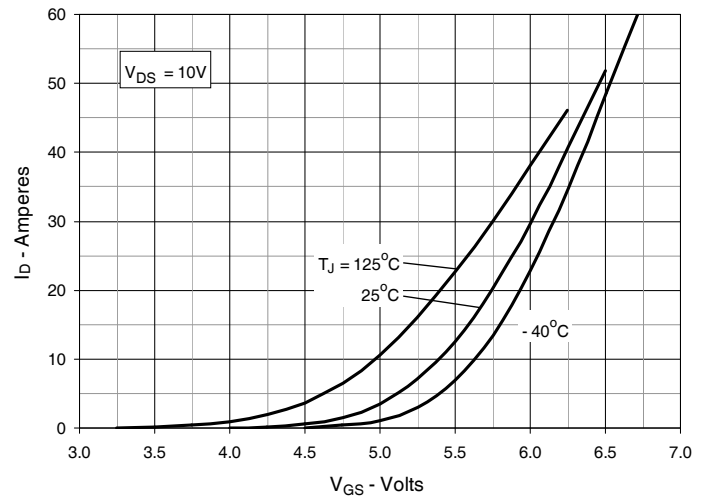
**Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature**



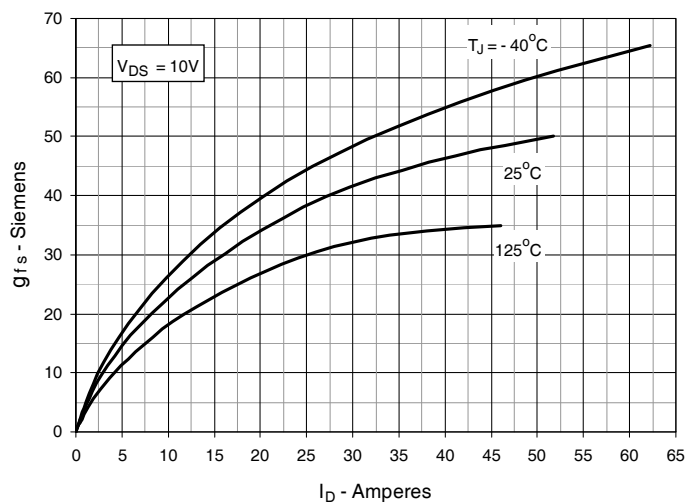
**Fig. 7. Maximum Drain Current vs. Case Temperature**



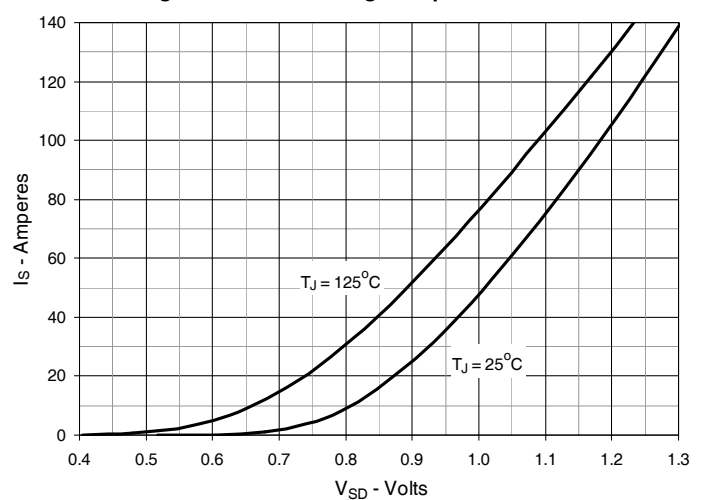
**Fig. 8. Input Admittance**



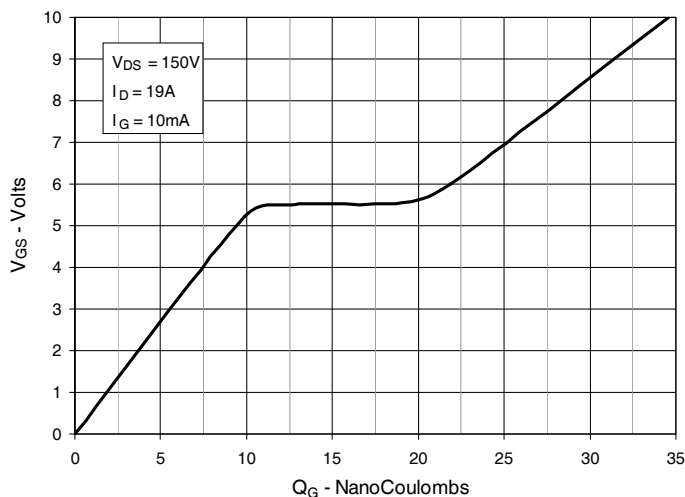
**Fig. 9. Transconductance**



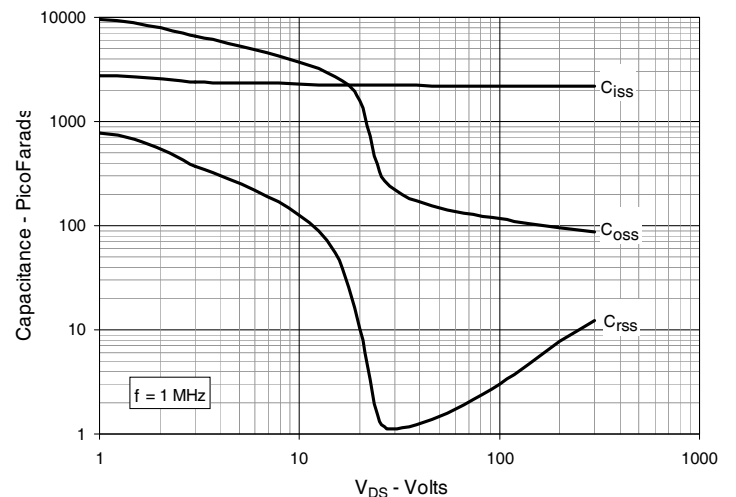
**Fig. 10. Forward Voltage Drop of Intrinsic Diode**



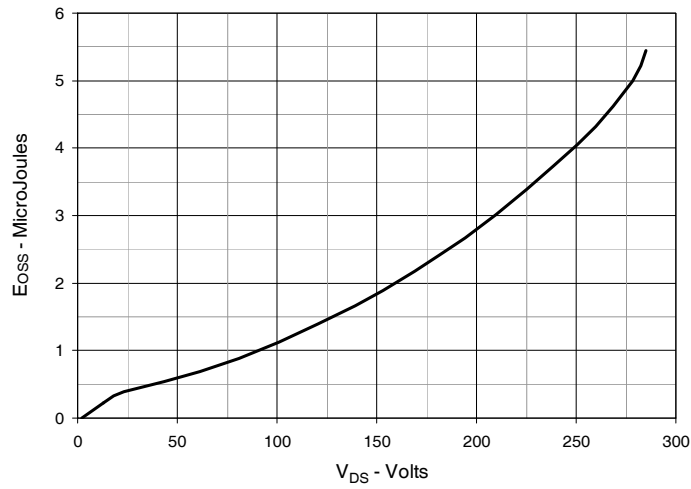
**Fig. 11. Gate Charge**



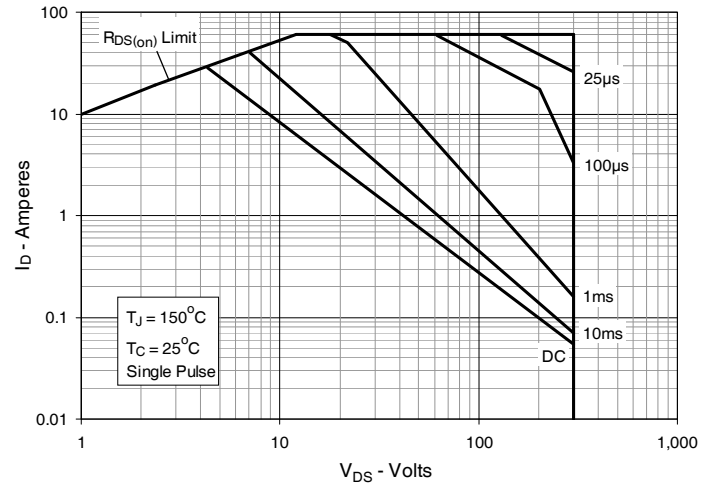
**Fig. 12. Capacitance**



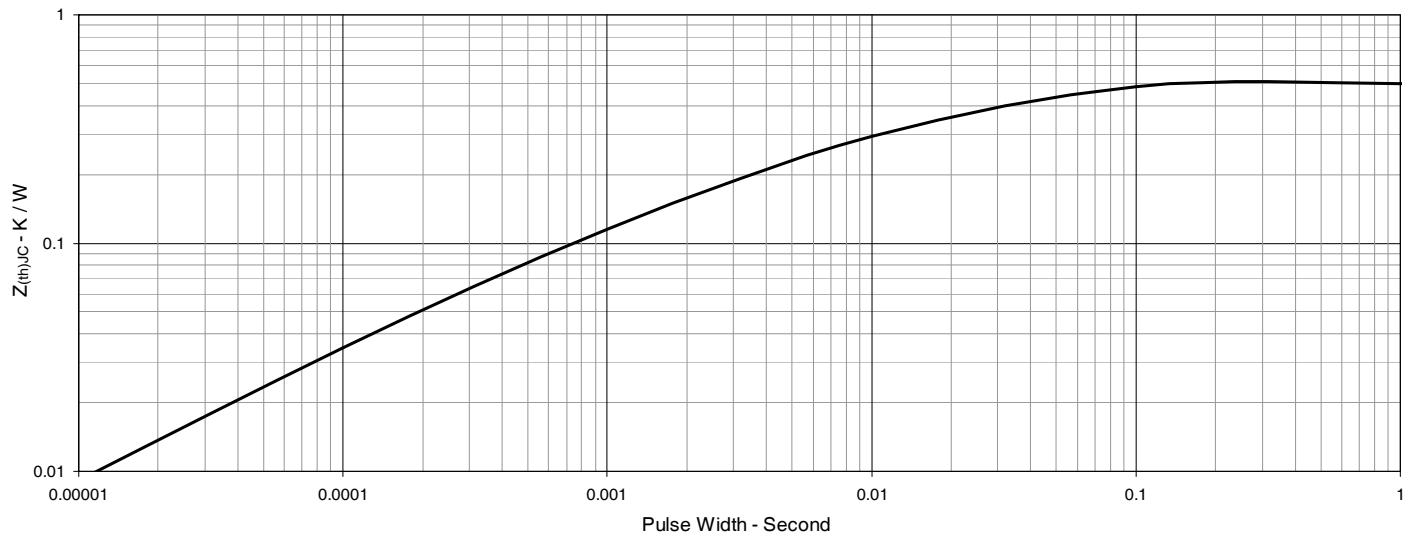
**Fig. 13. Output Capacitance Stored Energy**



**Fig. 14. Forward-Bias Safe Operating Area**



**Fig. 15. Maximum Transient Thermal Impedance**



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